# AN79Lxx/AN79LxxM Series

### 3-pin negative output voltage regulator (100 mA type)

#### Overview

The AN79Lxx series and the AN79LxxM series are 3-pin, fixed negative output type monolithic voltage regulators.

Stabilized fixed output voltage is obtained from unstable DC input voltage without using any external components. 12 types of output voltage are available: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20Vand -24V. They can be used widely in power circuits with current capacity of up to 100mA.

#### Features

- No external components
- Output voltage: -4V, -5V, -6V, -7V, -8V, -9V, -10V, -12V, -15V, -18V, -20V, -24V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit



Note) The packages (SSIP003-P-0000 and HSIP003-P-0000B) of this product will be changed to lead-free type (SSIP003-P-0000S and HSIP003-P-0000Q). See the new package dimensions section later of this datasheet.

#### ■ Block Diagram (AN79Lxx series)



Note) The number in ( ) shows the pin number for the AN79LxxM series.

#### Absolute Maximum Ratings at $T_a = 25^{\circ}C$

Parameter		Symbol	Rating	Unit
Input voltage		V	-35 *1	V
		$V_{I}$	-40 *2	V
Power dissipation		P <sub>D</sub>	650 *3	mW
Operating ambient temperature		T <sub>opr</sub>	-20 to +80	°C
Store on torrestore	AN79Lxx series	т	-55 to +150	20
Storage temperature	AN79LxxM series	T <sub>stg</sub>	-55 to +125	°C

\*1 AN79L04, AN79L05/M, AN79L06, AN79L07, AN79L08/M, AN79L09/M, AN79L10, AN79L12/M, AN79L15/M, AN79L18

\*2 AN79L20, AN79L24

\*3 Follow the derating curve. When  $T_j$  exceeds 150°C, the internal circuit cuts off the output. AN79LxxM series is mounted on a standard board (glass epoxy: 20mm × 20mm × t1.7mm with Cu foil of 1cm<sup>2</sup> or more).

#### Electrical Characteristics at $T_a = 25^{\circ}C$

#### • AN79L04 (-4V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-3.84	-4	-4.16	v
Output voltage tolerance	Vo	$V_{I} = -7$ to $-19V$ , $I_{O} = 1$ to $70mA$	-3.8		-4.2	V
Line regulation	REGIN	$V_{I} = -6$ to $-20V$ , $T_{j} = 25^{\circ}C$			80	mV
	KLOIN	$V_{I} = -7$ to $-17V$ , $T_{j} = 25^{\circ}C$			40	mV
L and regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		10	60	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$	_	4.5	30	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	_	3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -7$ to $-19V$ , $T_{j} = 25^{\circ}C$	_		0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$	_	—	0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		38		μV
Ripple rejection ratio	RR	$V_I = -7$ to $-17V$ , $f = 120Hz$ , $T_a = 25^{\circ}C$	55			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	$I_{O(Short)}$	$V_{I} = -35V, T_{j} = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		- 0.4		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_1 = -9V$ ,  $I_0 = 40$ mA,  $C_1 = 2\mu$ F,  $C_0 = 1\mu$ F,  $T_j = 0$  to  $125^{\circ}$ C

#### ■ Electrical Characteristics at T<sub>a</sub> = 25°C (continued)

#### • AN79L05, AN79L05M (-5V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-4.8	-5	-5.2	V
Output voltage tolerance	Vo	$V_{I} = -8$ to $-20V$ , $I_{O} = 1$ to $70mA$	-4.75	—	-5.25	v
Line regulation	REGIN	$V_{I} = -7$ to $-21V$ , $T_{j} = 25^{\circ}C$		—	100	mV
Line regulation	KEOIN	$V_I = -8$ to $-18V$ , $T_j = 25^{\circ}C$		—	50	mV
Load regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		11	60	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		5	30	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -8$ to $-20V$ , $T_{j} = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		40		μν
Ripple rejection ratio	RR	$V_I = -8$ to $-18V$ , $f = 120Hz$ , $T_a = 25^{\circ}C$	55			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		v
Output short-circuit current	I <sub>O(Short)</sub>	$V_{I} = -35V, T_{j} = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		- 0.4		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -10V$ ,  $I_O = 40$ mA,  $C_I = 2\mu$ F,  $C_O = 1\mu$ F,  $T_j = 0$  to  $125^{\circ}$ C (AN79L05) and  $T_j = 0$  to  $100^{\circ}$ C (AN79L05M)

#### • AN79L06 (-6V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-5.76	-6	-6.24	v
Output voltage tolerance	Vo	$V_{I} = -9$ to $-21V$ , $I_{O} = 1$ to $70mA$	-5.7	—	-6.3	V
Line regulation	REGIN	$V_{I} = -8$ to $-22V$ , $T_{j} = 25^{\circ}C$		—	120	mV
	KEGIN	$V_{I} = -9$ to $-19V$ , $T_{j} = 25^{\circ}C$			60	mV
Land regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		12	60	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		5.5	30	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -9$ to $-21V$ , $T_{j} = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		44		μV
Ripple rejection ratio	RR	$V_{I} = -9$ to $-19V$ , f = 120Hz, $T_{a} = 25^{\circ}C$	55			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		- 0.4		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -11V$ ,  $I_O = 40mA$ ,  $C_I = 2\mu F$ ,  $C_O = 1\mu F$ ,  $T_j = 0$  to  $125^{\circ}C$ 

#### Electrical Characteristics at $T_a = 25^{\circ}C$ (continued)

#### • AN79L07 (-7V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-6.72	-7	-7.28	V
Output voltage tolerance	Vo	$V_I = -10$ to $-22V$ , $I_O = 1$ to $70mA$	-6.65		-7.35	V
Line regulation	REGIN	$V_I = -9$ to $-23V$ , $T_j = 25^{\circ}C$			140	mV
Line regulation	KEUIN	$V_{\rm I}{=}{-}10$ to ${-}20V,T_{\rm j}{=}25^\circ C$			70	mV
Land manulation	REG <sub>L</sub> –	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		13	70	mV
Load regulation		$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$	—	6	40	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -10$ to $-22V$ , $T_{j} = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		48		μν
Ripple rejection ratio	RR	$V_I = -10$ to $-20V$ , $f = 120Hz$ , $T_a = 25^{\circ}C$	54			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8	_	V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		- 0.5		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -12V$ ,  $I_0 = 40$ mA,  $C_I = 2\mu$ F,  $C_0 = 1\mu$ F,  $T_j = 0$  to  $125^{\circ}$ C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-7.68	-8	-8.32	V
Output voltage tolerance	Vo	$V_{I} = -11$ to $-23V$ , $I_{O} = 1$ to $70mA$	-7.6		-8.4	V
Line regulation	REGIN	$V_I = -10$ to $-24V$ , $T_j = 25^{\circ}C$			160	mV
Line regulation	KLOIN	$V_{I} = -11$ to $-21V$ , $T_{j} = 25^{\circ}C$			80	mV
Load regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		15	80	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		7	40	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -11$ to $-23V$ , $T_{j} = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$	—	52	—	μV
Ripple rejection ratio	RR	$V_{I} = -11$ to $-21V$ , $f = 120Hz$ , $T_{a} = 25^{\circ}C$	54			dB
Minimum input/output voltage difference	$V_{\text{DIF}(min)}$	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0 \text{ to } 125^{\circ}C$		- 0.6		mV/°C

#### AN79L08, AN79L08M (-8V type)

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -14V$ ,  $I_O = 40$ mA,  $C_I = 2\mu$ F,  $C_O = 1\mu$ F,  $T_j = 0$  to  $125^{\circ}$ C (AN79L08) and  $T_j = 0$  to  $100^{\circ}$ C (AN79L08M)

#### ■ Electrical Characteristics at T<sub>a</sub> = 25°C (continued)

#### • AN79L09, AN79L09M (-9V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-8.64	-9	-9.36	V
Output voltage tolerance	Vo	$V_I = -12$ to $-24V$ , $I_O = 1$ to $70mA$	-8.55	_	-9.45	V
Line regulation	REGIN	$V_{I} = -11$ to $-25V$ , $T_{j} = 25^{\circ}C$		_	160	mV
Line regulation	KEGIN	$V_I = -12$ to $-22V$ , $T_j = 25^{\circ}C$		_	80	mV
Load regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		16	90	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		8	50	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -12$ to $-24V$ , $T_j = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		58		μV
Ripple rejection ratio	RR	$V_I = -12$ to $-22V$ , $f = 120Hz$ , $T_a = 25^{\circ}C$	53			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		v
Output short-circuit current	I <sub>O(Short)</sub>	$V_{I} = -35V, T_{j} = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$ , $T_j = 0$ to $125^{\circ}C$		- 0.6		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -15V$ ,  $I_O = 40$ mA,  $C_I = 2\mu$ F,  $C_O = 1\mu$ F,  $T_j = 0$  to  $125^{\circ}$ C (AN79L09) and  $T_j = 0$  to  $100^{\circ}$ C (AN79L09M)

#### • AN79L10 (-10V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-9.6	-10	-10.4	V
Output voltage tolerance	Vo	$V_I = -13$ to $-25V$ , $I_O = 1$ to $70mA$	-9.5		-10.5	V
Line regulation	REGIN	$V_{I} = -12$ to $-26V$ , $T_{j} = 25^{\circ}C$			160	mV
Line regulation	KLOIN	$V_I = -13$ to $-23V$ , $T_j = 25^{\circ}C$			80	mV
Load regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		17	100	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		9	50	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -13$ to $-25V$ , $T_{j} = 25^{\circ}C$		—	0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		—	0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		65		μν
Ripple rejection ratio	RR	$V_{I} = -13$ to $-23V$ , f = 120Hz, $T_{a} = 25^{\circ}C$	53			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		- 0.7		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -16V$ ,  $I_O = 40mA$ ,  $C_I = 2\mu F$ ,  $C_O = 1\mu F$ ,  $T_j = 0$  to  $125^{\circ}C$ 

#### Electrical Characteristics at $T_a = 25^{\circ}C$ (continued)

#### • AN79L12, AN79L12M (-12V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-11.5	-12	-12.5	V
Output voltage tolerance	Vo	$V_{I} = -15$ to $-27V$ , $I_{O} = 1$ to $70mA$	-11.4	—	-12.6	V
Line regulation	REGIN	$V_{I} = -14.5$ to $-30V$ , $T_{j} = 25^{\circ}C$		—	200	mV
Line regulation	KEOIN	$V_I = -15$ to $-25V$ , $T_j = 25^{\circ}C$		—	100	mV
Load regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		20	100	mV
	REGL	$I_0 = 1 \text{ to } 40 \text{mA}, T_j = 25^{\circ}\text{C}$		10	50	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	_	3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -15$ to $-27V$ , $T_{j} = 25^{\circ}C$	_		0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$	_	—	0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		75		μV
Ripple rejection ratio	RR	$V_{I} = -15$ to $-25V$ , $f = 120Hz$ , $T_{a} = 25^{\circ}C$	52			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$	_	0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_{I} = -35V, T_{j} = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		- 0.8		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -19V$ ,  $I_0 = 40$ mA,  $C_I = 2\mu$ F,  $C_0 = 1\mu$ F,  $T_j = 0$  to  $125^{\circ}$ C (AN79L12) and  $T_j = 0$  to  $100^{\circ}$ C (AN79L12M)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-14.4	-15	-15.6	V
Output voltage tolerance	Vo	$V_{I} = -18$ to $-28V$ , $I_{O} = 1$ to $70mA$	-14.25		-15.75	V
Line regulation	REGIN	$V_{I} = -17.5$ to $-33V$ , $T_{j} = 25^{\circ}C$			200	mV
Line regulation	KLOIN	$V_I = -18$ to $-28V$ , $T_j = 25^{\circ}C$			100	mV
I and monulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		25	130	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		12	60	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -18$ to $-30V$ , $T_j = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	$V_{no}$	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		90		μν
Ripple rejection ratio	RR	$V_{I} = -18$ to $-28V$ , $f = 120Hz$ , $T_{a} = 25^{\circ}C$	51			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		V
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		- 0.9		mV/°C

#### • AN79L15, AN79L15M (-15V type)

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -23V$ ,  $I_0 = 40$ mA,  $\tilde{C}_I = 2\mu$ F,  $C_0 = 1\mu$ F,  $\tilde{T}_j = 0$  to 125°C (AN79L15) and  $T_j = 0$  to 100°C (AN79L15M)

#### ■ Electrical Characteristics at T<sub>a</sub> = 25°C (continued)

#### • AN79L18 (-18V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-17.3	-18	-18.7	V
Output voltage tolerance	Vo	$V_{I} = -21$ to $-33V$ , $I_{O} = 1$ to $70mA$	-17.1		-18.9	V
Line regulation	REGIN	$V_I = -21$ to $-33V$ , $T_j = 25^{\circ}C$	_	—	200	mV
Life regulation	KLOIN	$V_{I} = -21$ to $-32V$ , $T_{j} = 25^{\circ}C$		—	100	mV
Load regulation	DEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		30	160	mV
	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$	_	15	80	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = -21$ to $-33V$ , $T_{j} = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		110		μV
Ripple rejection ratio	RR	$V_{I} = -22$ to $-32V$ , f = 120Hz, $T_{a} = 25^{\circ}C$	50			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		v
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		-1		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -27V$ ,  $I_O = 40$ mA,  $C_I = 2\mu$ F,  $C_O = 1\mu$ F,  $T_j = 0$  to  $125^{\circ}$ C

#### • AN79L20 (-20V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-19.2	-20	-20.8	v
Output voltage tolerance	Vo	$V_{I} = -23$ to $-35V$ , $I_{O} = 1$ to $70mA$	-19		-21	V
Line regulation	REGIN	$V_I = -23$ to $-35V$ , $T_j = 25^{\circ}C$			200	mV
Life regulation	KLOIN	$V_{I} = -24$ to $-34V$ , $T_{j} = 25^{\circ}C$			100	mV
Load regulation	PEC	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		35	180	mV
Load regulation	REGL	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		17	90	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -23$ to $-35V$ , $T_j = 25^{\circ}C$	—		0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$	—		0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		135		μν
Ripple rejection ratio	RR	$V_{I} = -24$ to $-34V$ , f = 120Hz, $T_{a} = 25^{\circ}C$	49			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8	—	V
Output short-circuit current	$I_{O(Short)}$	$V_{I} = -35V, T_{j} = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		-1		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -29V$ ,  $I_O = 40mA$ ,  $C_I = 2\mu F$ ,  $C_O = 1\mu F$ ,  $T_j = 0$  to  $125^{\circ}C$ 

#### Electrical Characteristics at $T_a = 25^{\circ}C$ (continued)

#### • AN79L24 (-24V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	-23	-24	-25	V
Output voltage tolerance	Vo	$V_{I} = -27$ to $-38V$ , $I_{O} = 1$ to $70mA$	-22.8		-25.2	V
Line regulation	REG <sub>IN</sub>	$V_I = -27$ to $-38V$ , $T_j = 25^{\circ}C$			200	mV
		$V_{I} = -27$ to $-37V$ , $T_{j} = 25^{\circ}C$			100	mV
Load regulation	REGL	$I_0 = 1$ to 100mA, $T_j = 25^{\circ}C$		40	200	mV
		$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$		20	100	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = -27$ to $-38V$ , $T_j = 25^{\circ}C$			0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 1$ to 40mA, $T_j = 25^{\circ}C$			0.1	mA
Output noise voltage	V <sub>no</sub>	$f = 10Hz$ to 100kHz, $T_a = 25^{\circ}C$		170		μV
Ripple rejection ratio	RR	$V_1 = -28$ to $-38V$ , f = 120Hz, $T_a = 25^{\circ}C$	49			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$T_j = 25^{\circ}C$		0.8		v
Output short-circuit current	$I_{O(Short)}$	$V_I = -35V, T_j = 25^{\circ}C$		200		mA
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$		-1		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = -33V$ ,  $I_O = 40mA$ ,  $C_I = 2\mu F$ ,  $C_O = 1\mu F$ ,  $T_j = 0$  to  $125^{\circ}C$ 

#### Main Characteristics



#### Main Characteristics (continued)



Basic Regulator Circuit

100

1k

Frequency f (Hz)

10k

100k

0 L 10



Connect  $C_I$  of  $2\mu F$  when the input line is long.  $C_0$  improves the transient response.  $1\mu F$ 

#### Usage Notes

1. Cautions for a basic circuit



- C<sub>I</sub>: When a wiring from a smoothing circuit to a three-pin regulator is long, it is likely to oscillate at output. A capacitor of  $0.1\mu$ F to  $0.47\mu$ F should be connected near an input pin.
- $C_0$ : Deadly needed to prevent from oscillation (0.33µF to 1.0µF). It is recommended to use a capacitor of a small internal impedance (ex. tantalum capacitor) when using it under a low temperature.

When any sudden change of load current is likely to occur, connect an electrolytic capacitor of  $10\mu$ F to  $100\mu$ F to improve a transitional response of output voltage.

D<sub>i</sub>: Normally unnecessary. But add it in the case that there is a residual voltage at the output capacitor Co even after switching off the supply power because a current is likely to flow into an output pin of the IC and damage the IC.

#### 2. Other caution items

1) Short-circuit between the input pin and GND pin

If the input pin is short-circuitted to GND or is cut off when a large capacitance capacitor has been connected to the IC's load, a voltage of a capacitor connected to an output pin is applied between input/output of the IC and this likely results in damage of the IC. It is necessary, therefore, to connect a diode, as shown in figure 2, to counter the reverse bias between input/output pins.



2) Floating of GND pin

If a GND pin is made floating in an operating mode, an unstabilized input voltage is outputted. In this case, a thermal protection circuit inside the IC does not normally operate. In this state, if the load is short-circuited or overloaded, it is likely to damage the IC.

#### Application Circuit Example



Note)  $V_{\rm O}$  varies due to sample to sample variation of  $I_{\rm Bias}$  . Never fail to adjust individually with  $R_{\rm 1}$  .

- New Package Dimensions (Unit: mm)
- SSIP003-P-0000S (Lead-free package)



• HSIP003-P-0000Q (Lead-free package)



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